

# FCD9N60NTM

## N-Channel SupreMOS® MOSFET

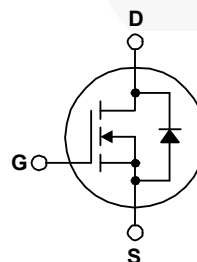
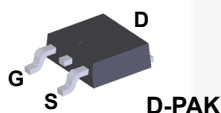
600 V, 9 A, 385 mΩ

### Features

- $R_{DS(on)} = 330 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 4.5 \text{ A}$
- Ultra Low Gate Charge (Typ.  $Q_g = 17.8 \text{ nC}$ )
- Low Effective Output Capacitance
- 100% Avalanche Tested
- RoHS Compliant

### Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest  $R_{sp}$  on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCD9N60NTM	Unit
$V_{DSS}$	Drain to Source Voltage	600	V
$V_{GSS}$	Gate to Source Voltage	$\pm 30$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	MOSFET dv/dt Ruggedness	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	15	
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	W
		- Derate above $25^\circ\text{C}$	W/°C
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	°C
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	FCD9N60NTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.35	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCD9N60NTM	FCD9N60NTM	D-PAK	Tape and Reel	330 mm	16 mm	2500 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 1\text{mA}$ , $V_{GS} = 0\text{V}$ , $T_J = 25^\circ\text{C}$	600	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{mA}$ , Referenced to $25^\circ\text{C}$	-	0.8	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{V}$ , $V_{GS} = 0\text{V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 480\text{V}$ , $V_{GS} = 0\text{V}$ , $T_C = 125^\circ\text{C}$	-	-	100	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 4.5\text{A}$	-	0.330	0.385	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{V}$ , $I_D = 4.5\text{A}$	-	5.3	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	735	1000	pF
$C_{oss}$	Output Capacitance		-	40	53	pF
$C_{rss}$	Reverse Transfer Capacitance		-	3.5	5.5	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	23.7	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{V}$ to $380\text{V}$ , $V_{GS} = 0\text{V}$	-	122	-	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{V}$ , $I_D = 4.5\text{A}$ $R_{GEN} = 4.7\Omega$ (Note 4)	-	13.2	-	ns
$t_r$	Turn-On Rise Time		-	9.6	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	28.7	-	ns
$t_f$	Turn-Off Fall Time		-	11.5	-	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{V}$ , $I_D = 4.5\text{A}$ $V_{GS} = 10\text{V}$ (Note 4)	-	17.8	-	nC
$Q_{gs}$	Gate to Source Gate Charge		-	4.2	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	7.6	-	nC
ESR	Equivalent Series Resistance(G-S)	$f = 1\text{MHz}$	-	2.65	-	$\Omega$

### Drain-Source Diode Characteristics

$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	9.0	-	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	27	-	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_{SD} = 9\text{A}$	-	-	1.2 V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}$ , $I_{SD} = 9\text{A}$	-	322	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$	-	5.04	$\mu\text{C}$

#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $I_{AS} = 3\text{A}$ ,  $R_G = 25\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 9\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq 380\text{V}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

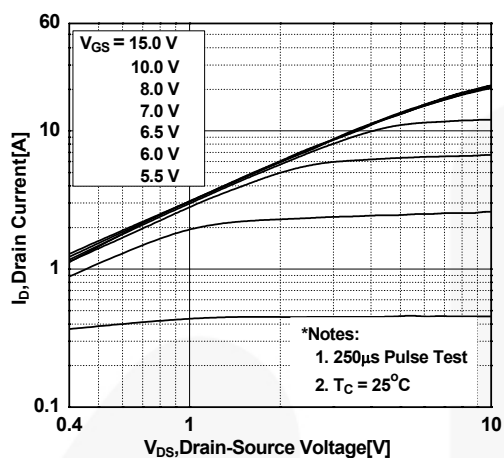


Figure 2. Transfer Characteristics

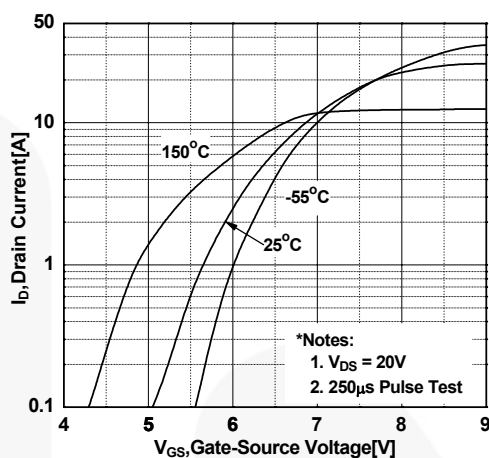


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

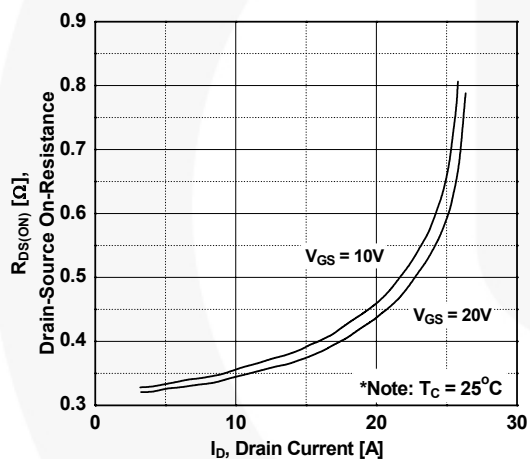


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

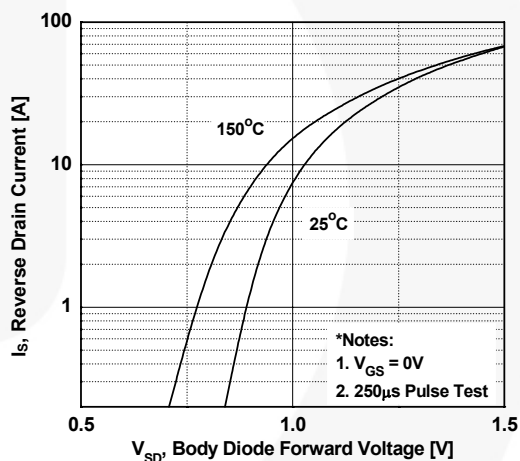


Figure 5. Capacitance Characteristics

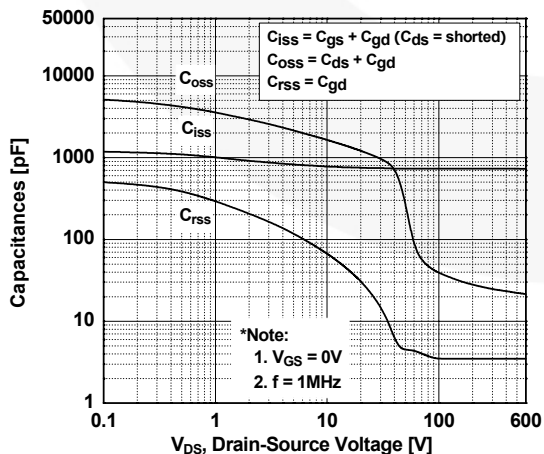
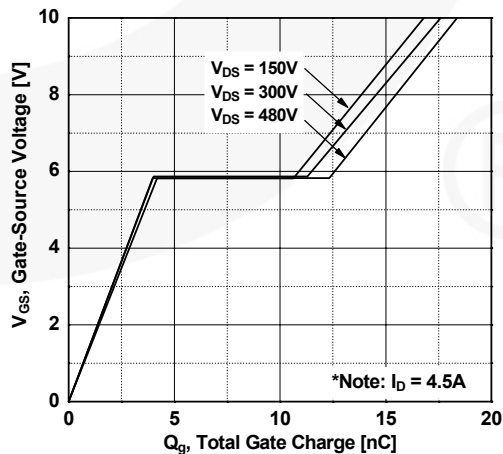


Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

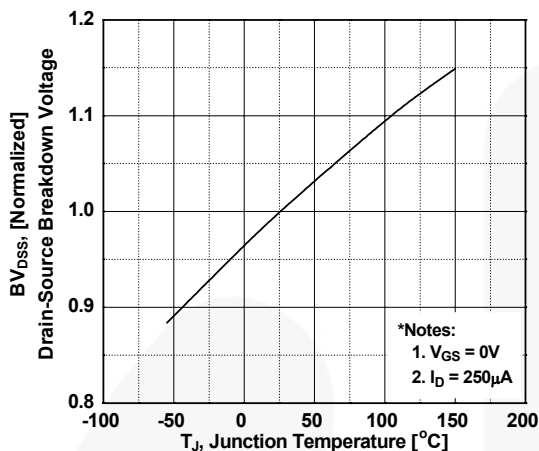


Figure 8. On-Resistance Variation vs. Temperature

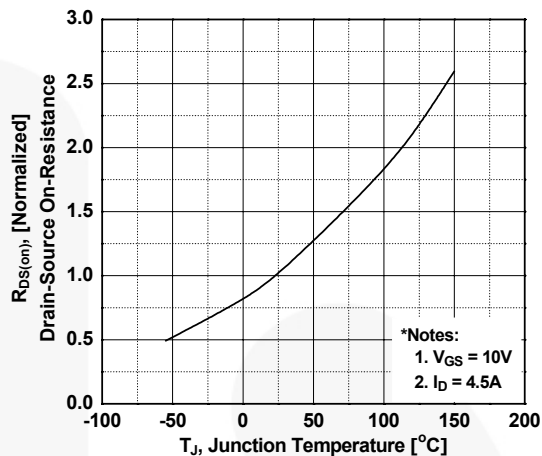


Figure 9. Maximum Safe Operating Area

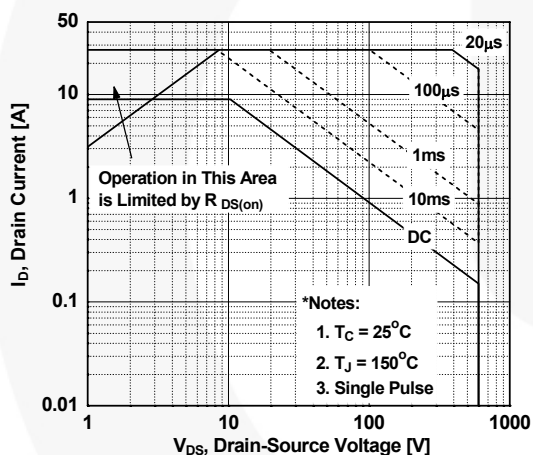


Figure 10. Maximum Drain Current vs. Case Temperature

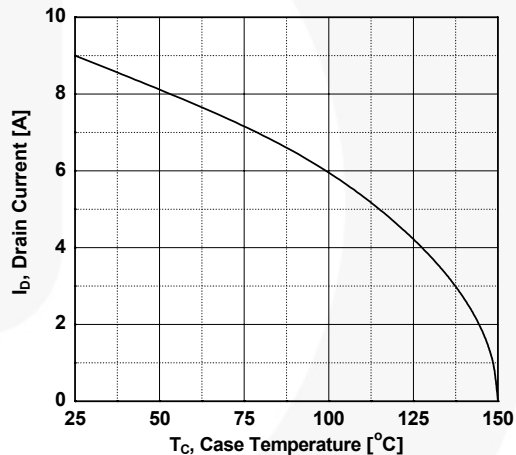


Figure 11. Transient Thermal Response Curve

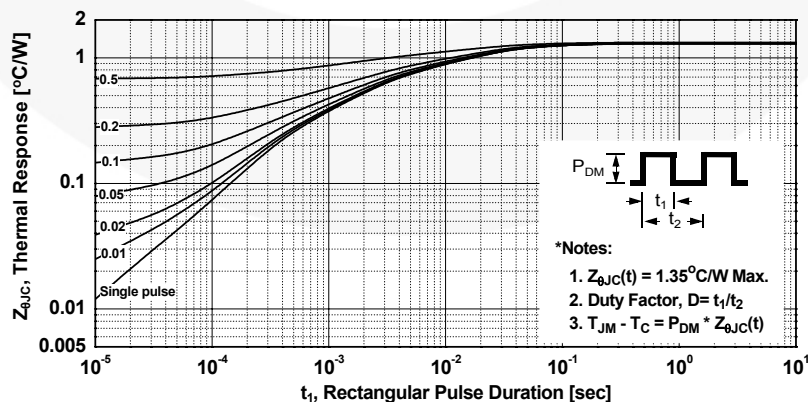




Figure 12. Gate Charge Test Circuit & Waveform

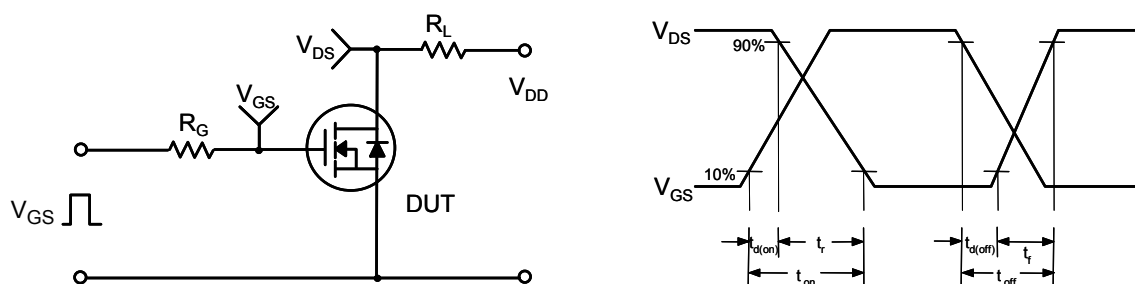


Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

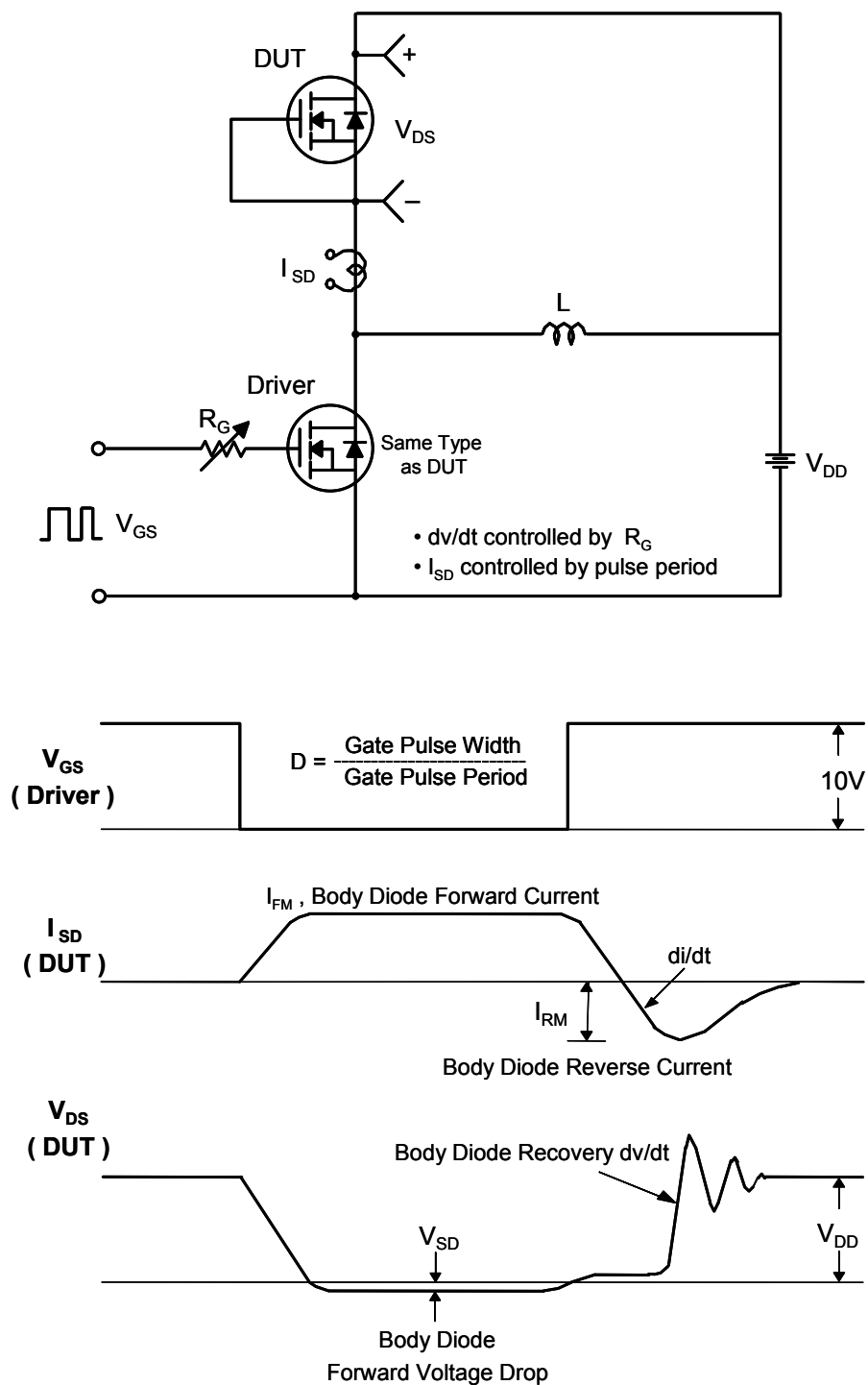
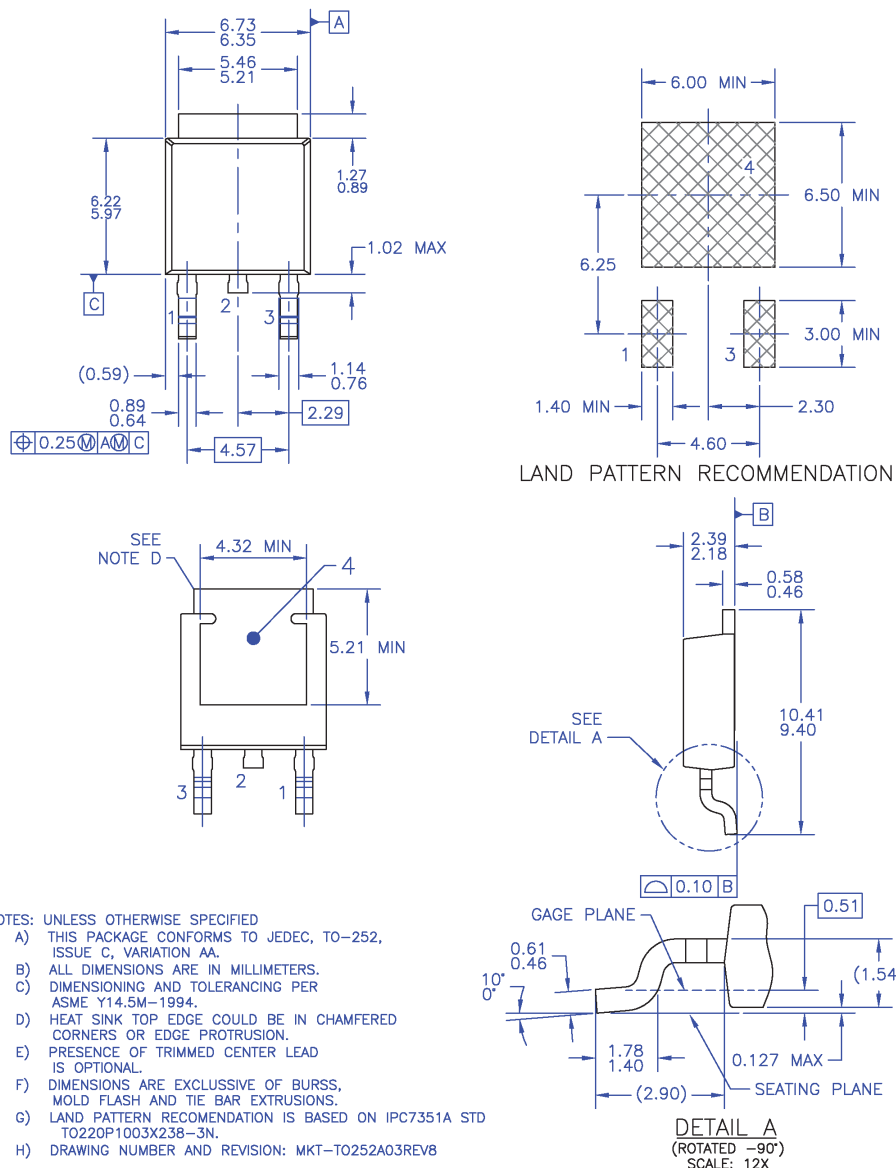


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

# Mechanical Dimensions



**Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB**

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